

ZXTP25100BFH

100V, SOT23, PNP medium power transistor

Summary

$BV_{(BR)CEX} > -140V$, $BV_{(BR)CEO} > -100V$

$BV_{(BR)ECX} > -7V$;

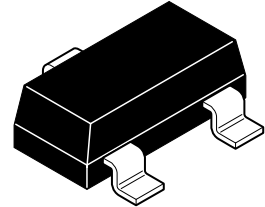
$I_{C(cont)} = -2A$

$V_{CE(sat)} < -130mV @ -1A$

$R_{CE(sat)} = 108m\Omega$ typical

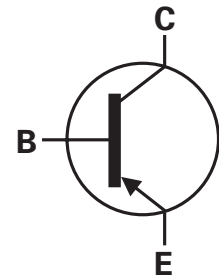
$P_D = 1.25W$

Complementary part number ZXTN25100BFH



Description

Advanced process capability and package design have been used to maximize the power handling and performance of this small outline transistor. The compact size and ratings of this device make it ideally suited to applications where space is at a premium.

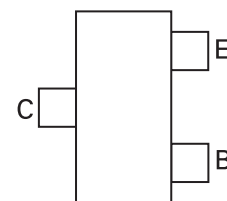


Features

- High power dissipation SOT23 package
- High peak current
- Low saturation voltage
- 140V forward blocking voltage
- 7V reverse blocking voltage

Applications

- MOSFET and IGBT gate driving
- DC - DC converters
- Motor drive
- Relay, lamp, and solenoid drive



Pinout - top view

Ordering information

Device	Reel size (inches)	Tape width	Quantity per reel
ZXTP25100BFHTA	7	8mm	3,000

Device marking

056

ZXTP25100BFH

Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-base voltage	V_{CBO}	-140	V
Collector-emitter voltage (forward blocking)	V_{CEX}	-140	V
Collector-emitter voltage	V_{CEO}	-100	V
Emitter-collector voltage (reverse blocking)	V_{ECX}	-7	V
Emitter-base voltage	V_{EBO}	-7	V
Continuous collector current ^(b)	I_C	-2	A
Peak pulse current	I_{CM}	-5	A
Power dissipation at $T_A = 25^\circ\text{C}$ ^(a) Linear derating factor	P_D	0.73 5.84	W mW/°C
Power dissipation at $T_A = 25^\circ\text{C}$ ^(b) Linear derating factor	P_D	1.05 8.4	W mW/°C
Power dissipation at $T_A = 25^\circ\text{C}$ ^(c) Linear derating factor	P_D	1.25 9.6	W mW/°C
Power dissipation at $T_A = 25^\circ\text{C}$ ^(d) Linear derating factor	P_D	1.81 14.5	W mW/°C
Operating and storage temperature range	T_j, T_{stg}	-55 to 150	°C

Thermal resistance

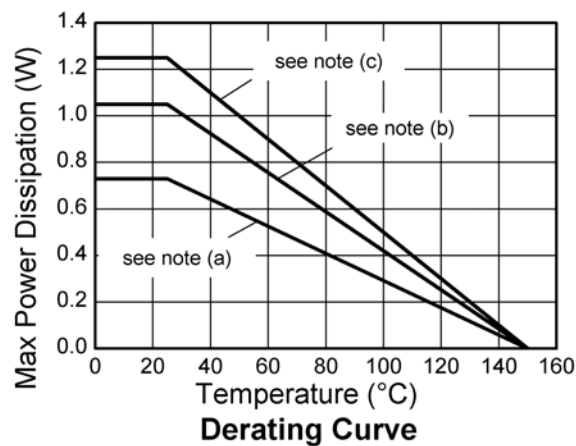
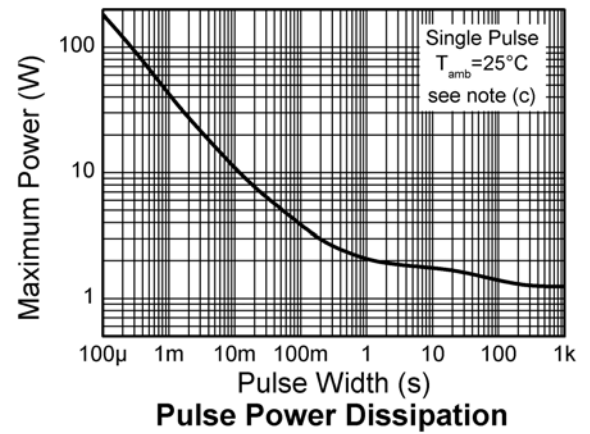
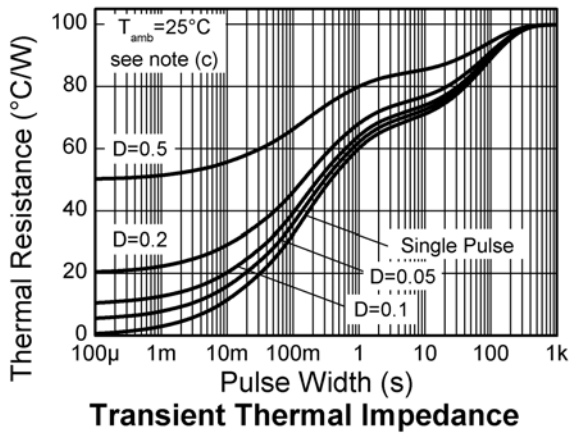
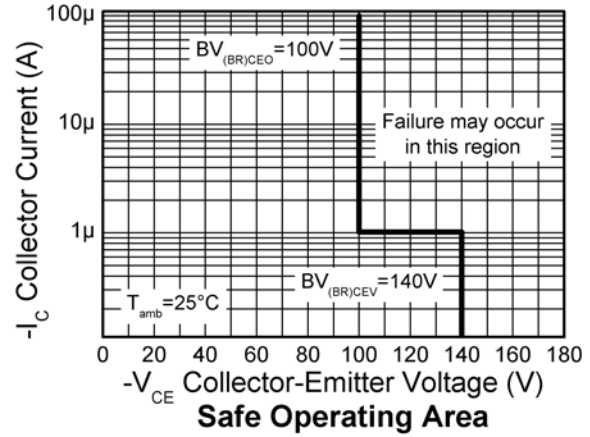
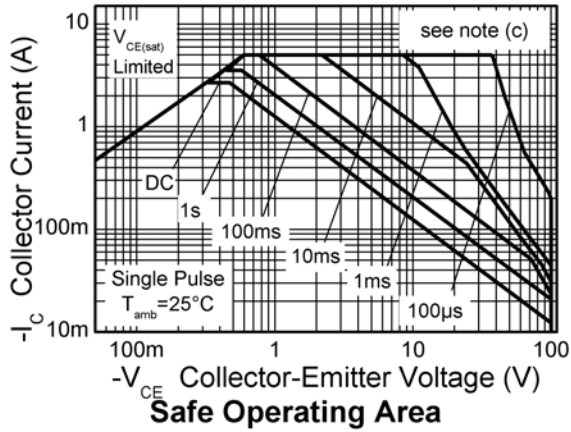
Parameter	Symbol	Limit	Unit
Junction to ambient ^(a)	$R_{\theta JA}$	171	°C/W
Junction to ambient ^(b)	$R_{\theta JA}$	119	°C/W
Junction to ambient ^(c)	$R_{\theta JA}$	100	°C/W
Junction to ambient ^(d)	$R_{\theta JA}$	69	°C/W

NOTES:

- (a) For a device surface mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- (b) Mounted on 25mm x 25mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.
- (c) Mounted on 50mm x 50mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.
- (d) As (c) above measured at $t < 5$ secs.

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Characteristics



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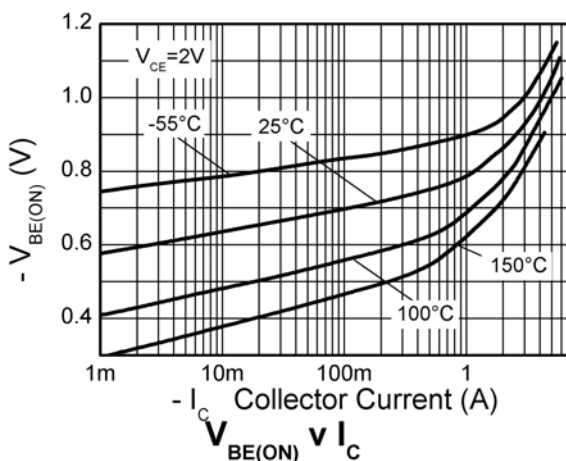
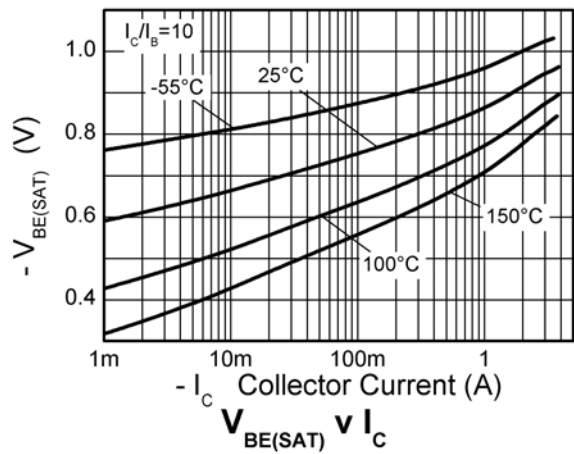
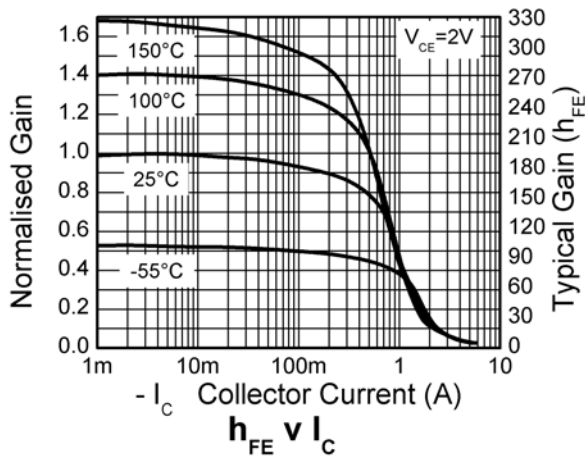
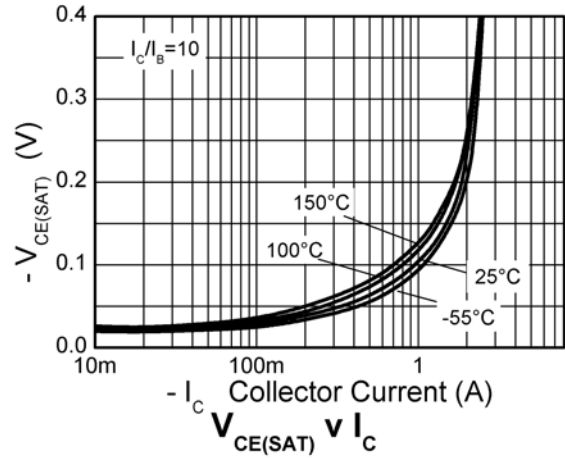
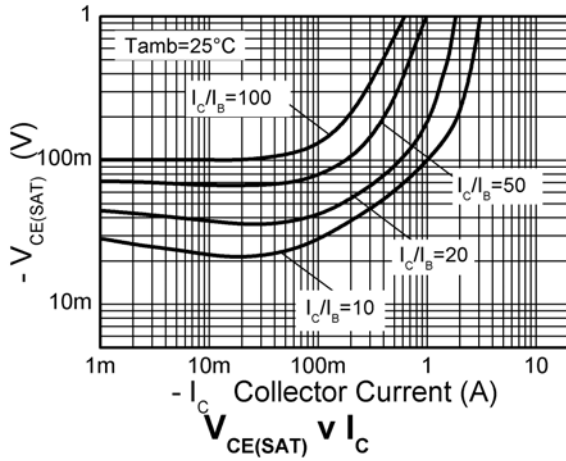
Electrical characteristics (at $T_{AMB} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	-140	-165		V	$I_C = -100\mu\text{A}$
Collector-emitter breakdown voltage (forward blocking)	BV_{CEX}	-140	-165		V	$I_C = -100\mu\text{A}$, $R_{BE} < 1\text{k}\Omega$ or $-0.25\text{V} < V_{BE} < 1\text{V}$
Collector-emitter breakdown voltage (base open)	BV_{CEO}	-100	-125		V	$I_C = -10\text{mA}^{(*)}$
Emitter-collector breakdown voltage (reverse blocking)	BV_{ECX}	-7	8.2		V	$I_E = -100\mu\text{A}$, $R_{BC} < 1\text{k}\Omega$ or $-0.25\text{V} < V_{BC} < 0.25\text{V}$
Emitter-base breakdown voltage	BV_{EBO}	-7	-8.2		V	$I_E = -100\mu\text{A}$
Collector cut-off current	I_{CBO}		<-1	-50 -20	nA μA	$V_{CB} = -112\text{V}$ $V_{CB} = -112\text{V}$, $T_{AMB} = 100^{\circ}\text{C}$
Collector emitter cut-off current	I_{CEX}		-	-100	nA	$V_{CE} = -112\text{V}$; $R_{BE} < 1\text{k}\Omega$ or $-0.25\text{V} < V_{BE} < 1\text{V}$
Emitter cut-off current	I_{EBO}		<-1	-50	nA	$V_{EB} = -5.6\text{V}$
Collector-emitter saturation voltage	$V_{CE(sat)}$		-60	-90	mV	$I_C = -0.5\text{A}$, $I_B = -50\text{mA}^{(*)}$
			-240	-350	mV	$I_C = -0.5\text{A}$, $I_B = -10\text{mA}^{(*)}$
			-100	-130	mV	$I_C = -1\text{A}$, $I_B = -100\text{mA}^{(*)}$
			-215	-295	mV	$I_C = -2\text{A}$, $I_B = -200\text{mA}^{(*)}$
Base-emitter saturation voltage	$V_{BE(sat)}$		-900	-1000	mV	$I_C = -2\text{A}$, $I_B = -200\text{mA}^{(*)}$
Base-emitter turn-on voltage	$V_{BE(on)}$		-830	-950	mV	$I_C = -2\text{A}$, $V_{CE} = -2\text{V}^{(*)}$
Static forward current transfer ratio	h_{FE}	100	200	300		$I_C = -10\text{mA}$, $V_{CE} = -2\text{V}^{(*)}$
		55	105			$I_C = -1\text{A}$, $V_{CE} = -2\text{V}^{(*)}$
		15	25			$I_C = -2\text{A}$, $V_{CE} = -2\text{V}^{(*)}$
Transition frequency	f_T		200		MHz	$I_C = -100\text{mA}$, $V_{CE} = -5\text{V}$ $f = 100\text{MHz}$
Output capacitance	C_{OBO}		15	25	pF	$V_{CB} = -10\text{V}$, $f = 1\text{MHz}^{(*)}$
Turn-on time	$t_{(on)}$		31		ns	$V_{CC} = -10\text{V}$, $I_C = -500\text{mA}$,
Turn-off time	$t_{(off)}$		384		ns	$I_{B1} = I_{B2} = -50\text{mA}$

NOTES:

(*) Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.

Typical characteristics



ZXTP25100BFH

Package outline - SOT23



Dim.	Millimeters		Inches		Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Max.	Max.
A	2.67	3.05	0.105	0.120	H	0.33	0.51	0.013	0.020
B	1.20	1.40	0.047	0.055	K	0.01	0.10	0.0004	0.004
C	-	1.10	-	0.043	L	2.10	2.50	0.083	0.0985
D	0.37	0.53	0.015	0.021	M	0.45	0.64	0.018	0.025
F	0.085	0.15	0.0034	0.0059	N	0.95 NOM		0.0375 NOM	
G	1.90 NOM		0.075 NOM		-	-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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